

74HC253; 74HCT253

Dual 4-input multiplexer; 3-state

Rev. 5 — 21 January 2015

Product data sheet

1. General description

The 74HC253; 74HCT253 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC253; 74HCT253 provides a dual 4-input multiplexer with 3-state outputs which selects 2 bits of data from up to four sources selected by common data select inputs (S0, S1). The two 4-input multiplexer circuits have individual active LOW output enable inputs ($\overline{1OE}$, $\overline{2OE}$).

The 74HC253 and 74HCT253 are the logic implementation of a 2-pole, 4-position switch, where the position of the switch is determined by the logic levels applied to S0 and S1. The outputs are forced to a high-impedance OFF-state when $\overline{nOE}$ is HIGH.

The logic equations for the outputs are:

$$1Y = \overline{1OE} \cdot (1I0 \cdot \overline{S1} \cdot \overline{S0} + 1I1 \cdot \overline{S1} \cdot S0 + 1I2 \cdot S1 \cdot \overline{S0} + 1I3 \cdot S1 \cdot S0)$$

$$2Y = \overline{2OE} \cdot (2I0 \cdot \overline{S1} \cdot \overline{S0} + 2I1 \cdot \overline{S1} \cdot S0 + 2I2 \cdot S1 \cdot \overline{S0} + 2I3 \cdot S1 \cdot S0)$$

2. Features and benefits

- Non-inverting data path
- 3-state outputs interface directly with system bus
- Complies with JEDEC standard no. 7A
- Common select inputs
- Separate output enable inputs
- Input levels:
 - ◆ For 74HC253: CMOS level
 - ◆ For 74HCT253: TTL level
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C



3. Applications

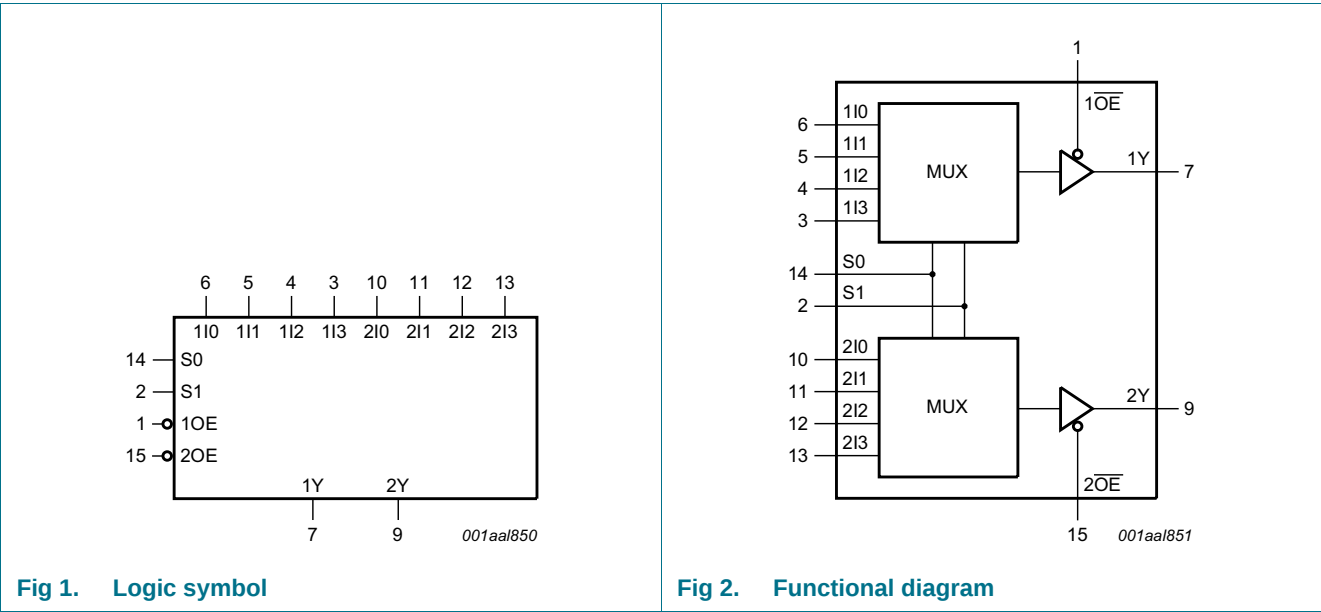
- Data selectors
- Data multiplexers

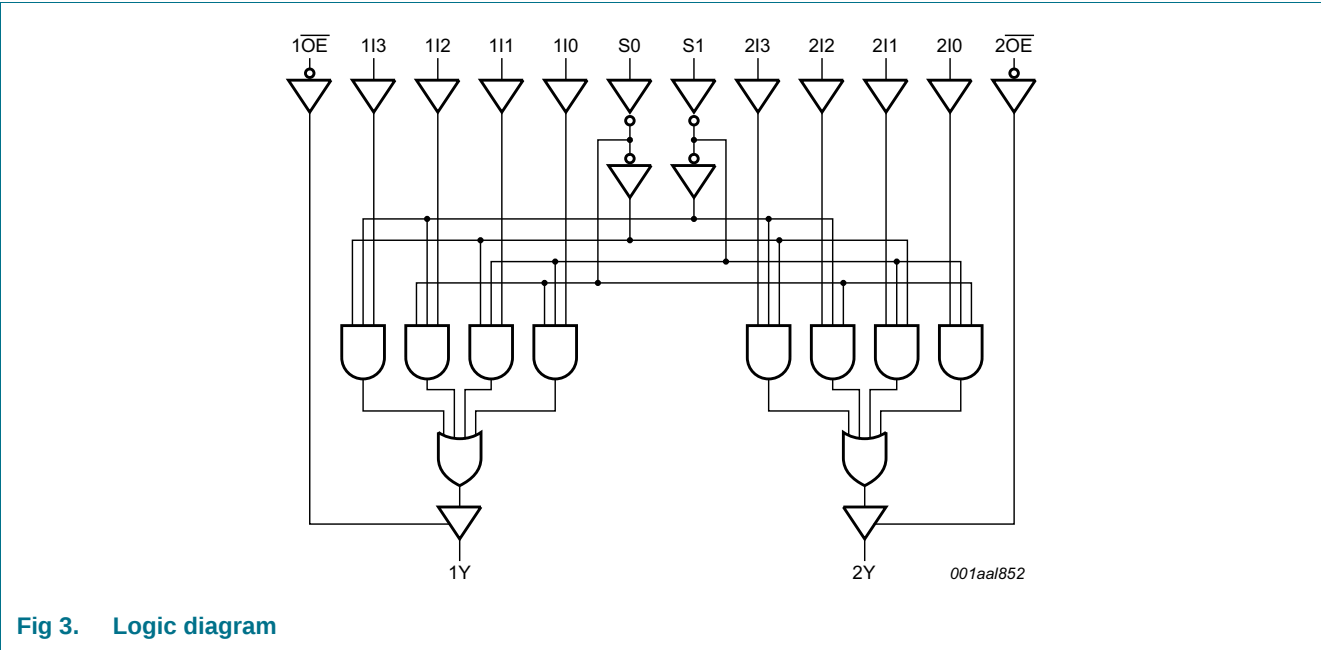
4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC253N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT253N				
74HC253D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT253D				
74HC253DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT253DB				

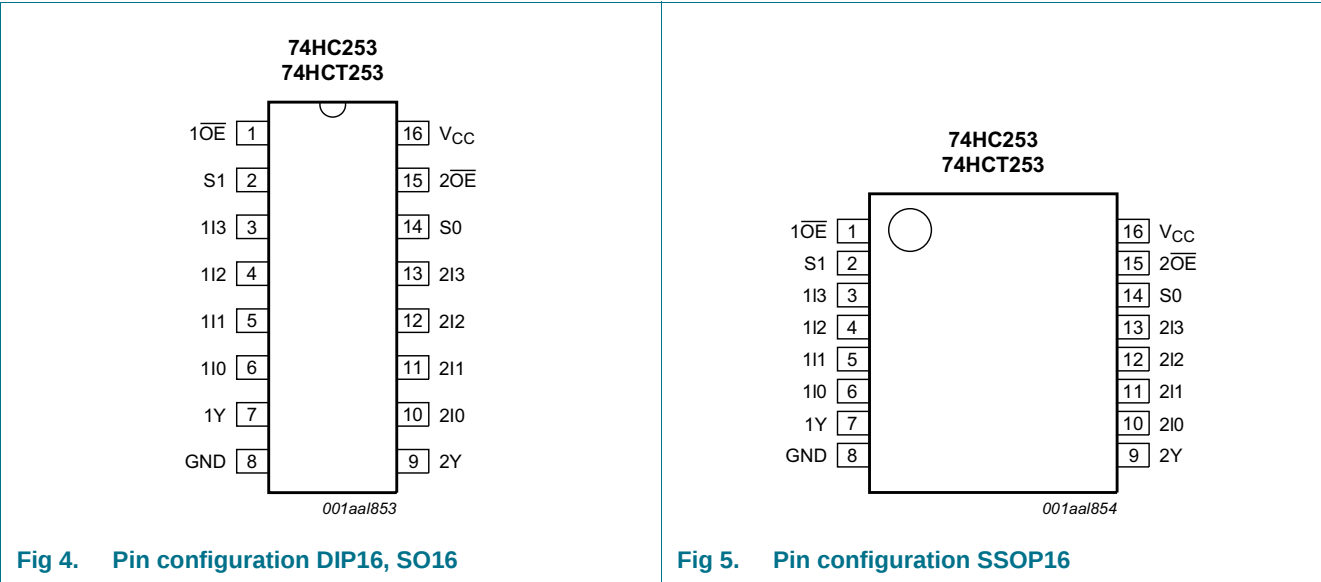
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{1OE}, \overline{2OE}$	1, 15	output enable inputs (active LOW)
S0, S1	14, 2	data select inputs
1I0, 1I1, 1I2, 1I3	6, 5, 4, 3	data inputs source 1
1Y	7	multiplexer output source 1
GND	8	ground (0 V)
2Y	9	multiplexer output source 2
2I0, 2I1, 2I2, 2I3	10, 11, 12, 13	data inputs source 2
V _{CC}	16	supply voltage

7. Functional description

Table 3. Function table^[1]

select inputs		data inputs				output enable	output
S0	S1	nI0	nI1	nI2	nI3	nOE	nY
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	L
L	L	H	X	X	X	L	H
H	L	X	L	X	X	L	L
H	L	X	H	X	X	L	H
L	H	X	X	L	X	L	L
L	H	X	X	H	X	L	H
H	H	X	X	X	L	L	L
H	H	X	X	X	H	L	H

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±50	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C			
		DIP16 package [2]	-	750	mW
		SO16 package [3]	-	500	mW
		SSOP16 package [4]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.[3] P_{tot} derates linearly with 8 mW/K above 70 °C.[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC253			74HCT253			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC253										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA
C _I	input capacitance		-	3.5	-					pF
74HCT253										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; V _O = V _{CC} or GND per input pin; other inputs at V _{CC} or GND; I _O = 0 A	-	-	±0.5	-	±5.0	-	±10	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	µA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1\text{ V}$; other inputs at V_{CC} or GND; $V_{CC} = 4.5\text{ V}$ to 5.5 V ; $I_O = 0\text{ A}$								
		per input pin; 1In, 2In inputs	-	40	144	-	180	-	196	μA
		per input pin; $\overline{nOE}$ input	-	110	396	-	495	-	539	μA
		per input pin; Sn input	-	110	396	-	495	-	539	μA
C_i	input capacitance		-	3.5	-					pF

11. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C		–40 °C to +85 °C	–40 °C to +125 °C	Unit
			Typ	Max	Max	Max	
74HC253							
t _{pd}	propagation delay	1In to 1Y or 2In to 2Y; see Figure 6 [1]					
		V _{CC} = 2.0 V	55	175	220	265	ns
		V _{CC} = 4.5 V	20	35	44	53	ns
		V _{CC} = 5.0 V; C _L = 15 pF	17	-	-	-	ns
		V _{CC} = 6.0 V	16	30	37	45	ns
		Sn to nY; see Figure 6					
		V _{CC} = 2.0 V	58	175	220	265	ns
		V _{CC} = 4.5 V	21	35	44	53	ns
		V _{CC} = 5.0 V; C _L = 15 pF	18	-	-	-	ns
		V _{CC} = 6.0 V	17	30	37	45	ns
t _{en}	enable time	$\overline{\text{nOE}}$ to nY; see Figure 7 [2]					
		V _{CC} = 2.0 V	30	100	125	150	ns
		V _{CC} = 4.5 V	11	20	25	30	ns
		V _{CC} = 6.0 V	9	17	21	26	ns
t _{dis}	disable time	$\overline{\text{nOE}}$ to nY; see Figure 7 [3]					
		V _{CC} = 2.0 V	41	150	190	225	ns
		V _{CC} = 4.5 V	15	30	38	45	ns
		V _{CC} = 6.0 V	12	26	33	38	ns
t _t	transition time	see Figure 6 [4]					
		V _{CC} = 2.0 V	14	60	75	90	ns
		V _{CC} = 4.5 V	5	12	15	18	ns
		V _{CC} = 6.0 V	4	10	13	15	ns

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C		–40 °C to +85 °C	–40 °C to +125 °C	Unit
			Typ	Max	Max	Max	
C _{PD}	power dissipation capacitance	per multiplexer; [5] V _I = GND to V _{CC}	55	-			pF
74HCT253							
t _{pd}	propagation delay	1In to 1Y or 2In to 2Y; [1] see Figure 6					
		V _{CC} = 4.5 V	20	38	48	57	ns
		V _{CC} = 5.0 V; C _L = 15 pF	17	-	-		ns
		Sn to nY; see Figure 6					
		V _{CC} = 4.5 V	22	40	50	60	ns
		V _{CC} = 5.0 V; C _L = 15 pF	19	-			ns
t _{en}	enable time	n $\overline{\text{OE}}$ to nY; V _{CC} = 4.5 V; [2] see Figure 7	14	30	38	45	ns
t _{dis}	disable time	n $\overline{\text{OE}}$ to nY; V _{CC} = 4.5 V; [3] see Figure 7	13	30	38	45	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	5	12	15	18	ns
C _{PD}	power dissipation capacitance	per multiplexer; [5] V _I = GND to V _{CC} – 1.5 V	55	-			pF

[1] t_{pd} is the same as t_{PHL}, t_{PLH}.

[2] t_{en} is the same as t_{PZH}, t_{PZL}.

[3] t_{dis} is the same as t_{PHZ}, t_{PLZ}.

[4] t_t is the same as t_{THL}, t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms

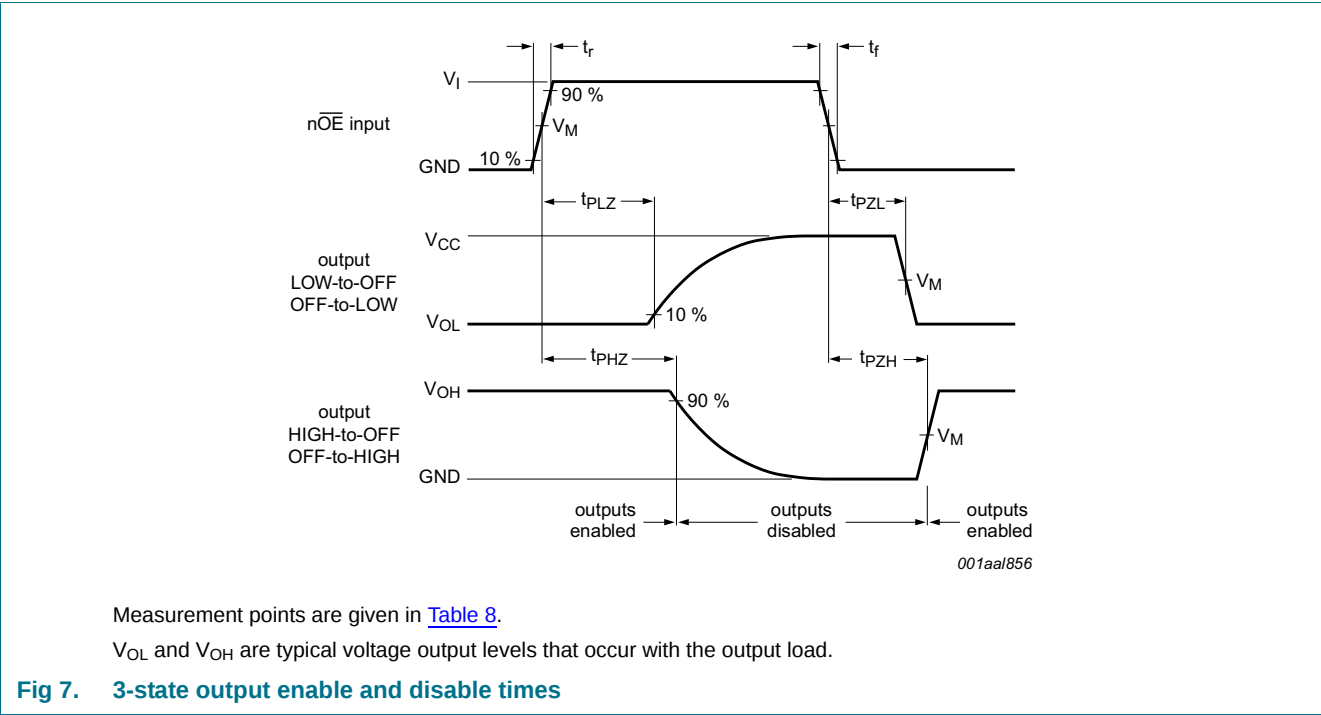
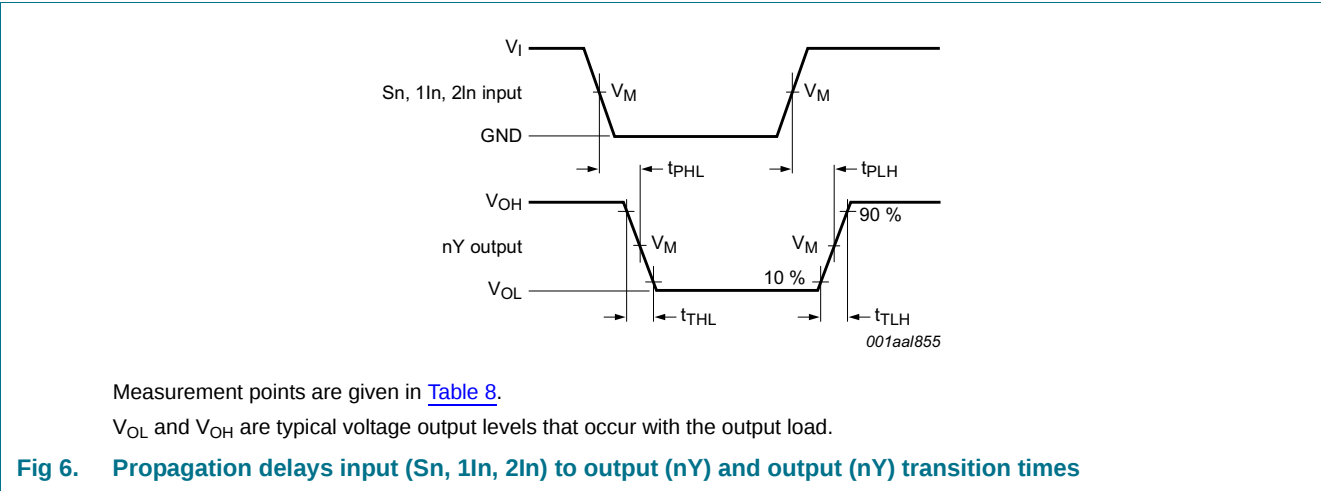


Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC253	$0.5V_{CC}$	$0.5V_{CC}$
74HCT253	1.3 V	1.3 V

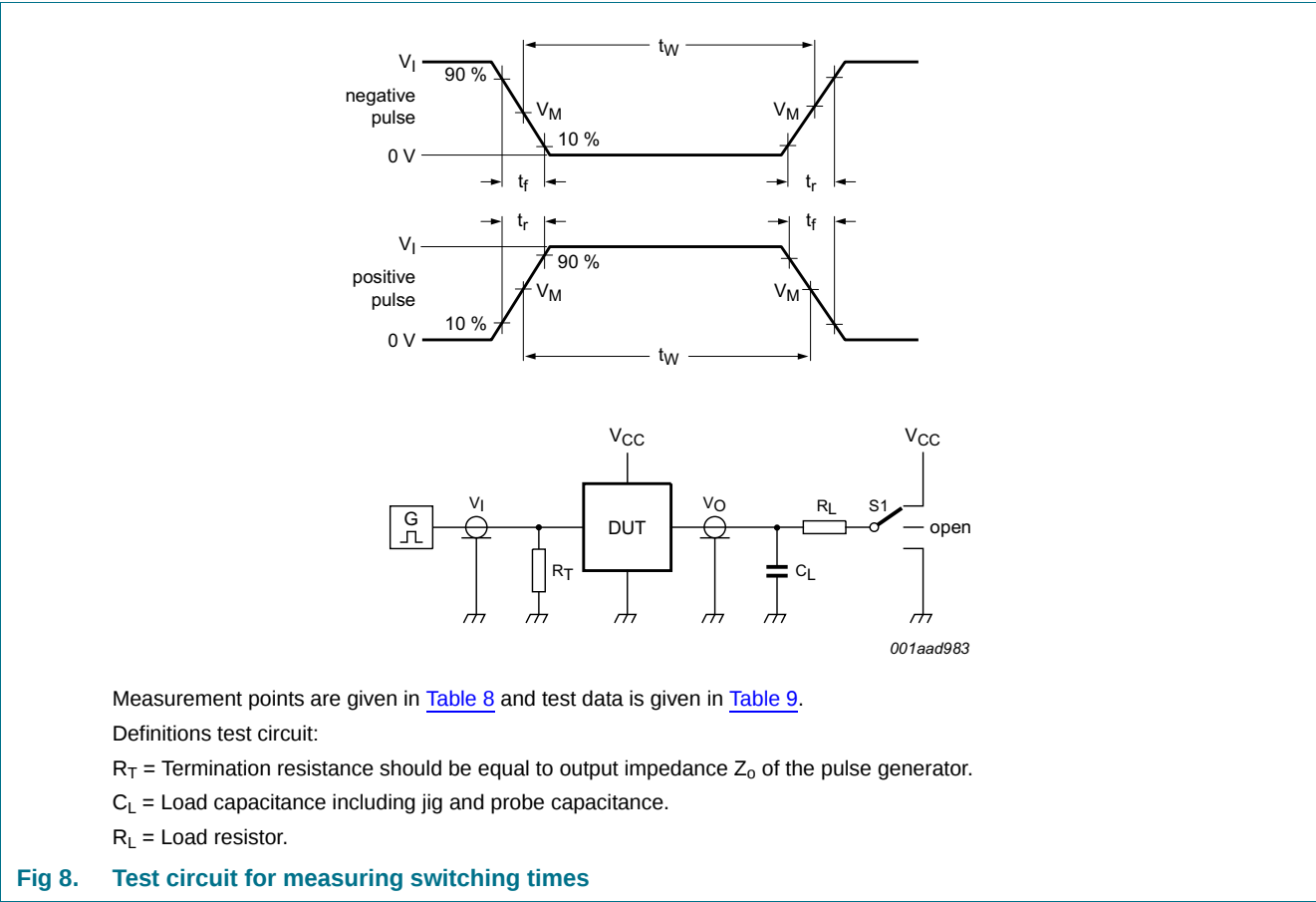


Table 9. Test data

Type	Input		Load		Switch position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC253	V_{CC}	6 ns	50 pF	1 k Ω	open	GND	V_{CC}
74HCT253	3 V	6 ns	50 pF	1 k Ω	open	GND	V_{CC}

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

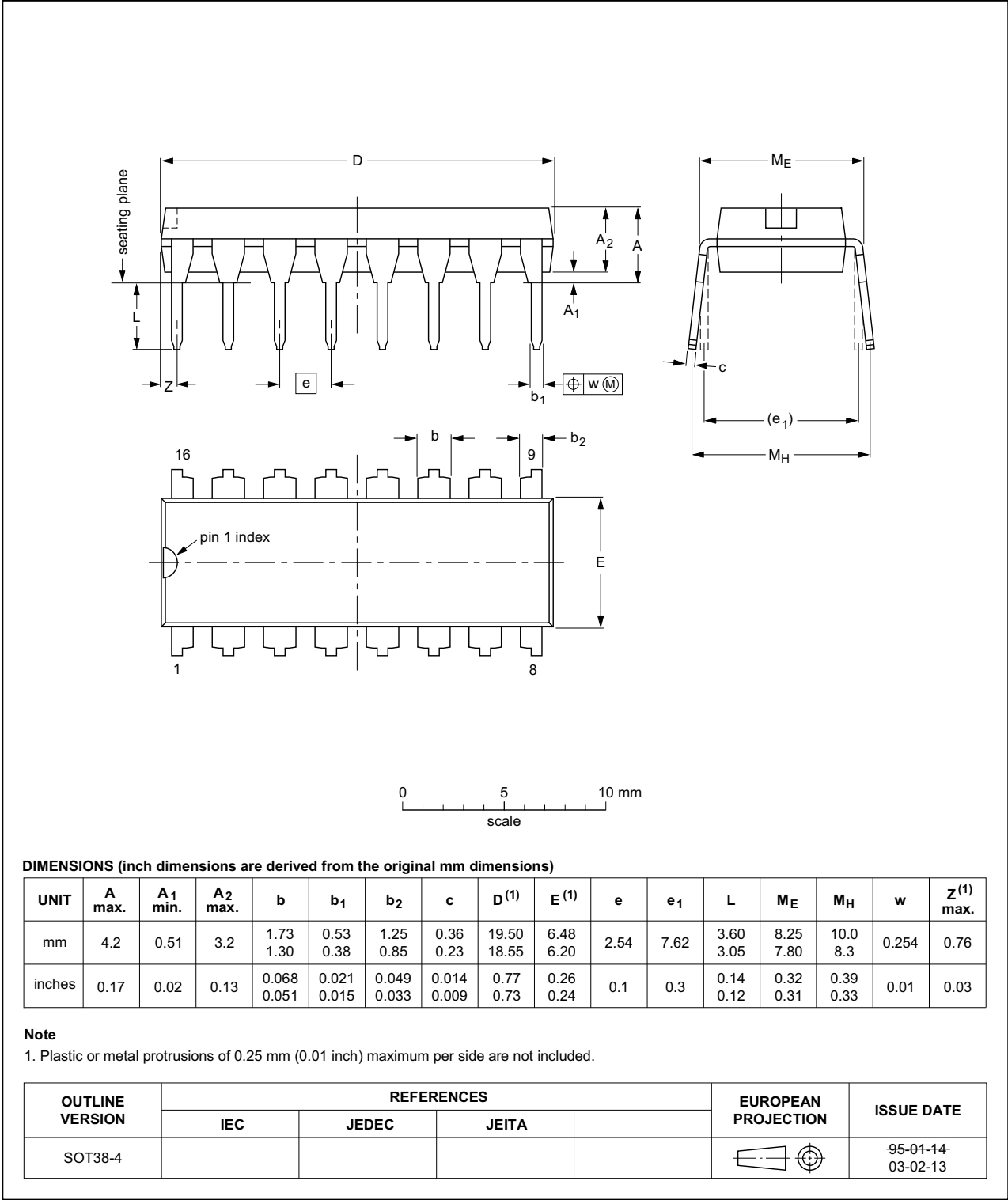


Fig 9. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

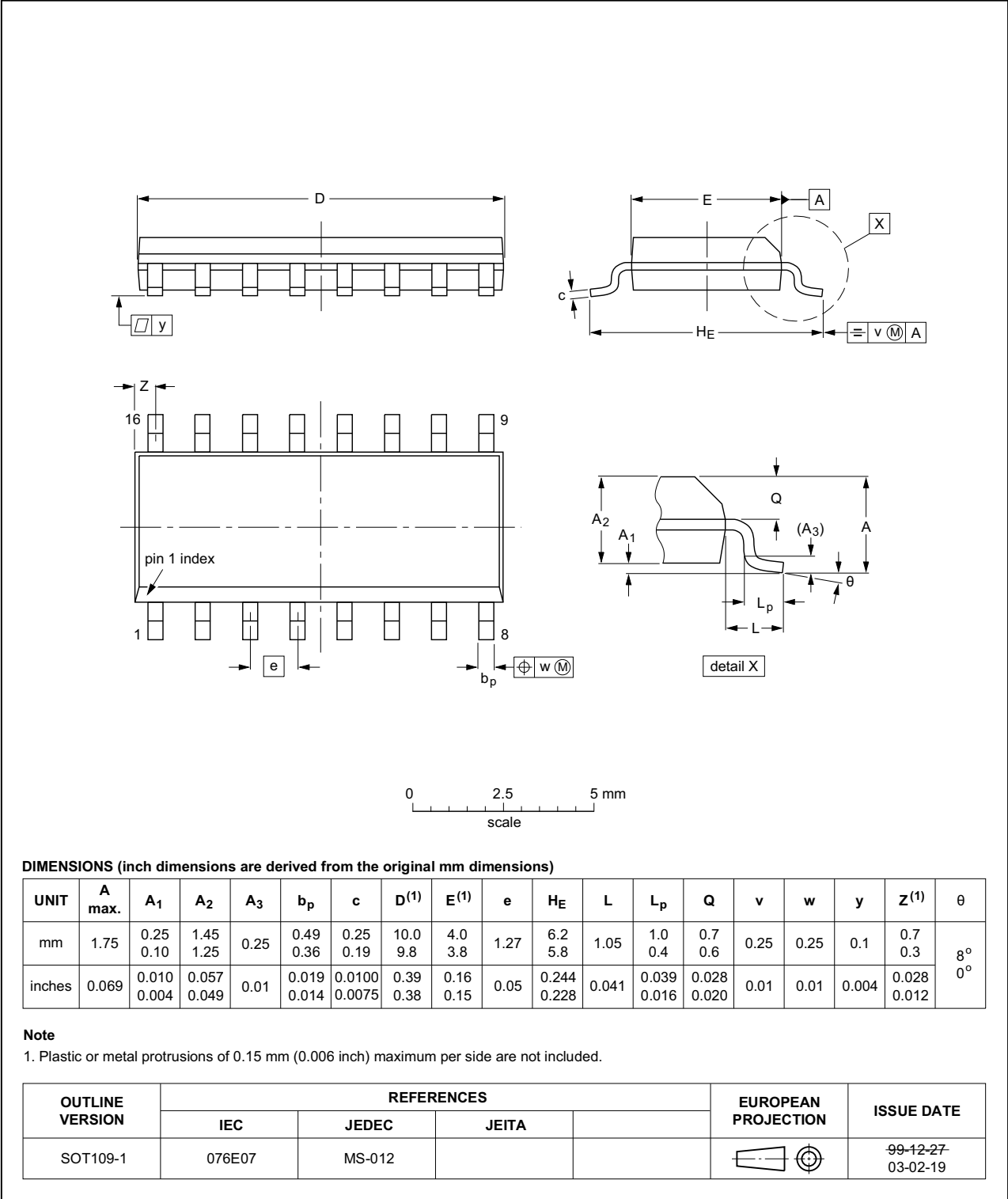


Fig 10. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

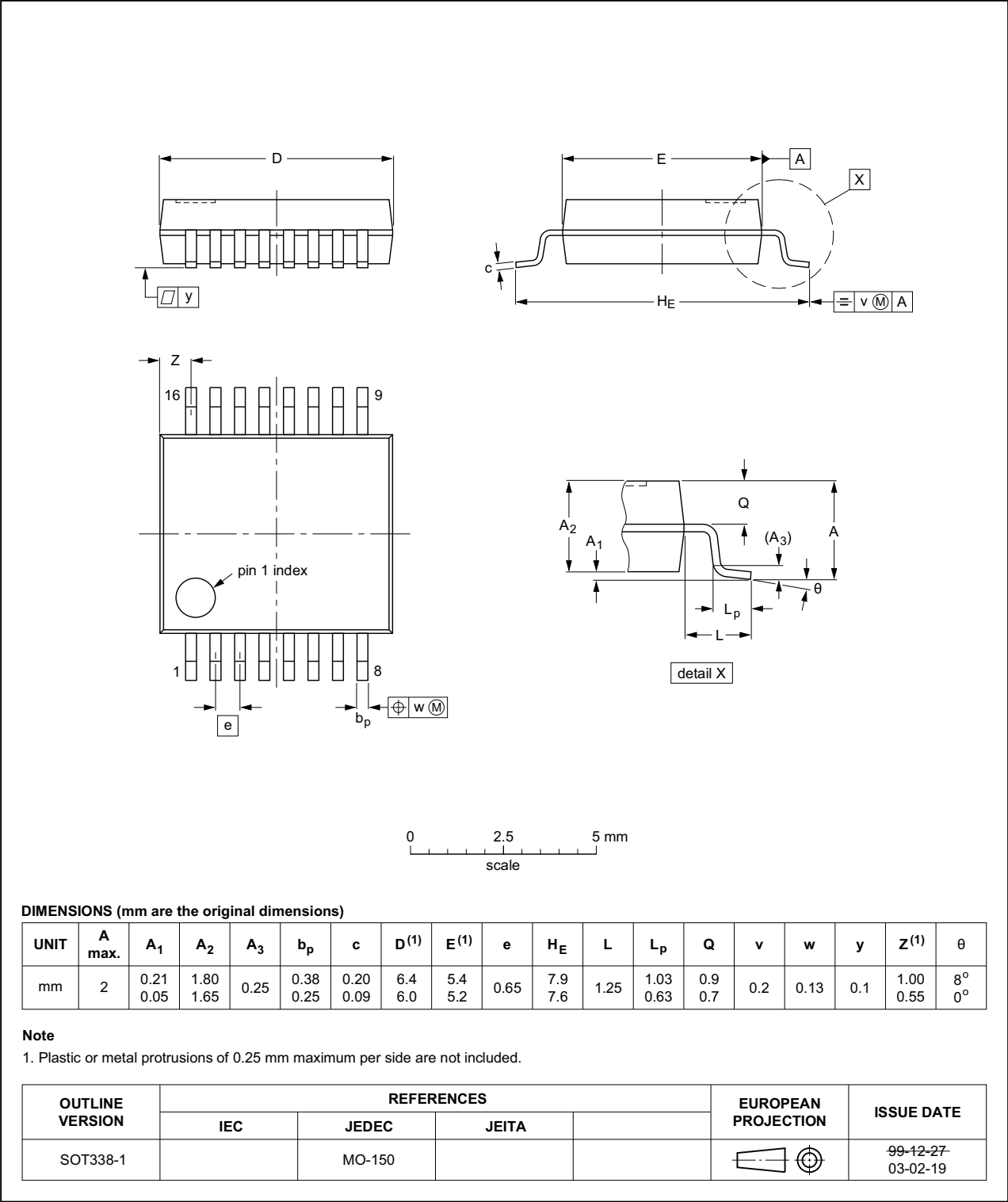


Fig 11. Package outline SOT338-1 (SSOP16)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT253 v.5	20150121	Product data sheet	-	74HC_HCT253 v.4
Modifications:	• Table 7 : Power dissipation capacitance condition for 74HCT253 is corrected.			
74HC_HCT253 v.4	20111212	Product data sheet	-	74HC_HCT253 v.3
Modifications:	• Legal pages updated.			
74HC_HCT253 v.3	20100422	Product data sheet	-	74HC_HCT253_CNV v.2
74HC_HCT253_CNV v.2	970828	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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